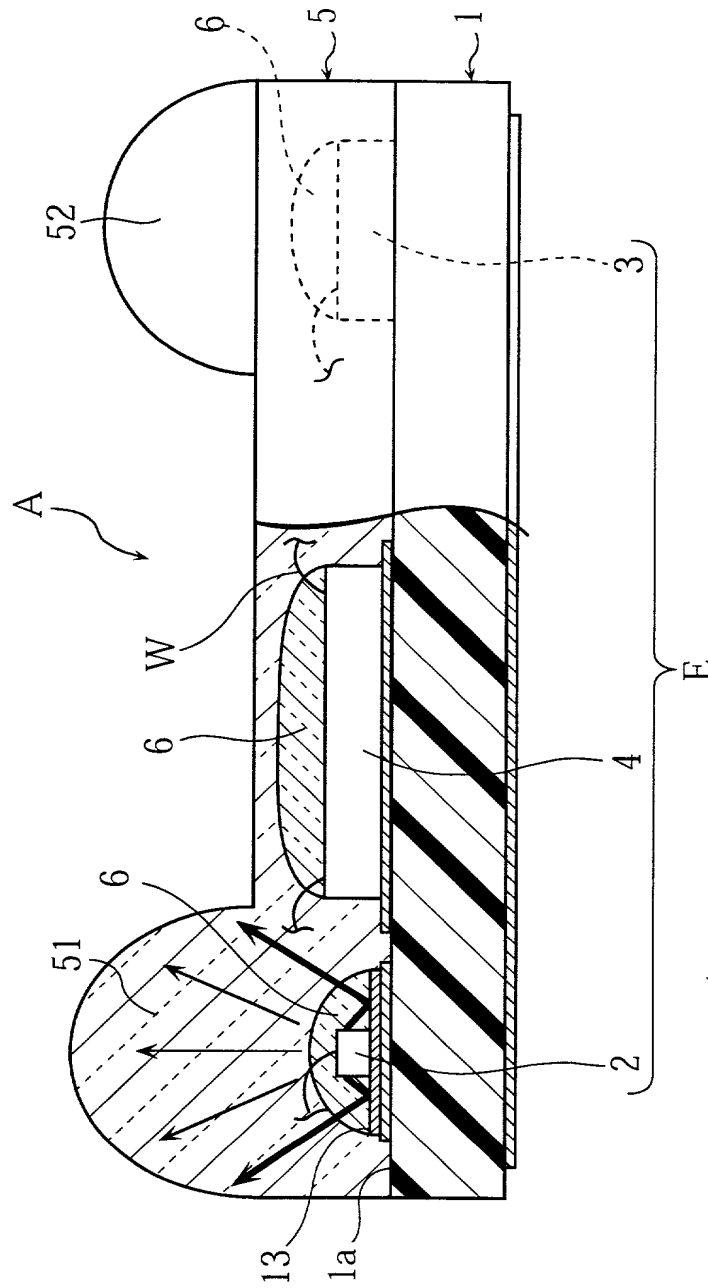




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A detailed cross-sectional diagram of a semiconductor device. The structure consists of several stacked layers. At the top, there are two main regions labeled 11a and 11b, which appear to be gate electrodes or similar structures. Below these are various conductive and insulating layers, some of which are patterned. A central region contains a large circular feature, possibly a well or a cavity, surrounded by different materials. Various other components like contacts, vias, and interconnects are shown throughout the stack. Numerous numerical labels (e.g., 1, 2, 3, 7, 8, 10, 11a, 11b, 12a, 12b, 13, 14, 19) point to specific parts of the device.

FIG. 4

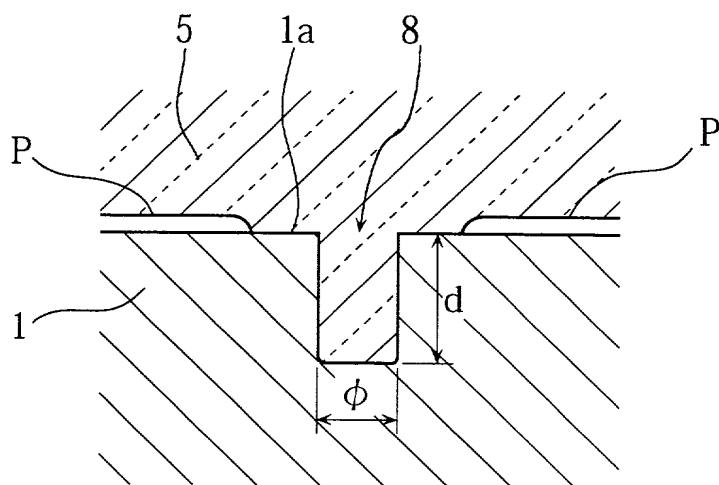


FIG. 5

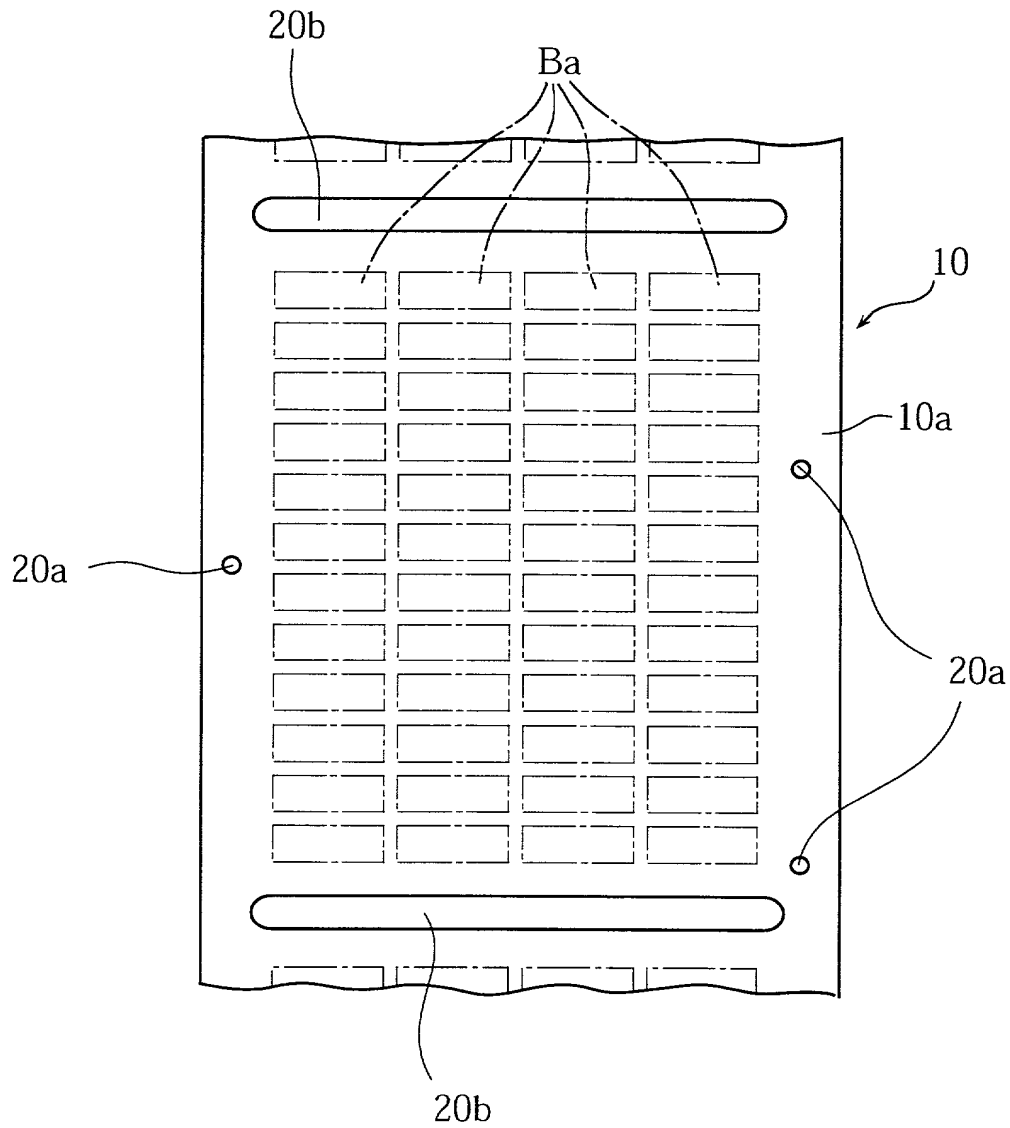


FIG. 6

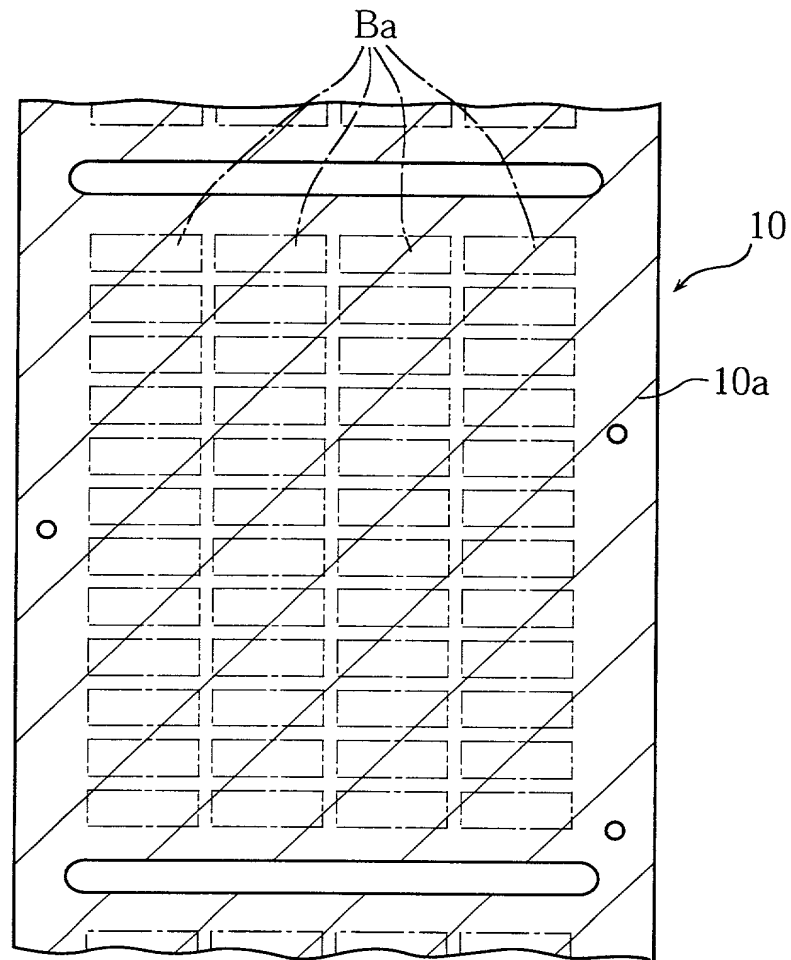








FIG. 9

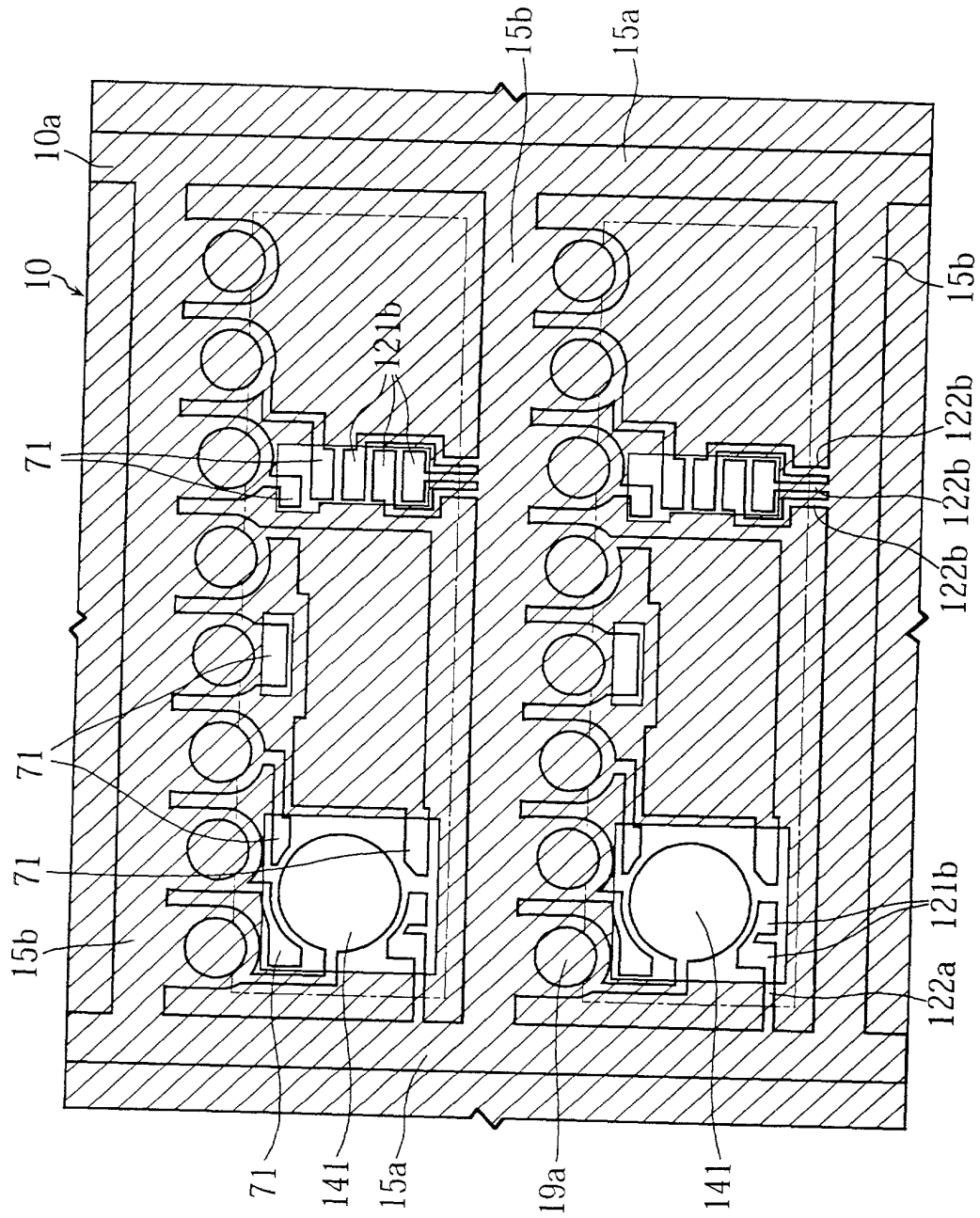


FIG. 10

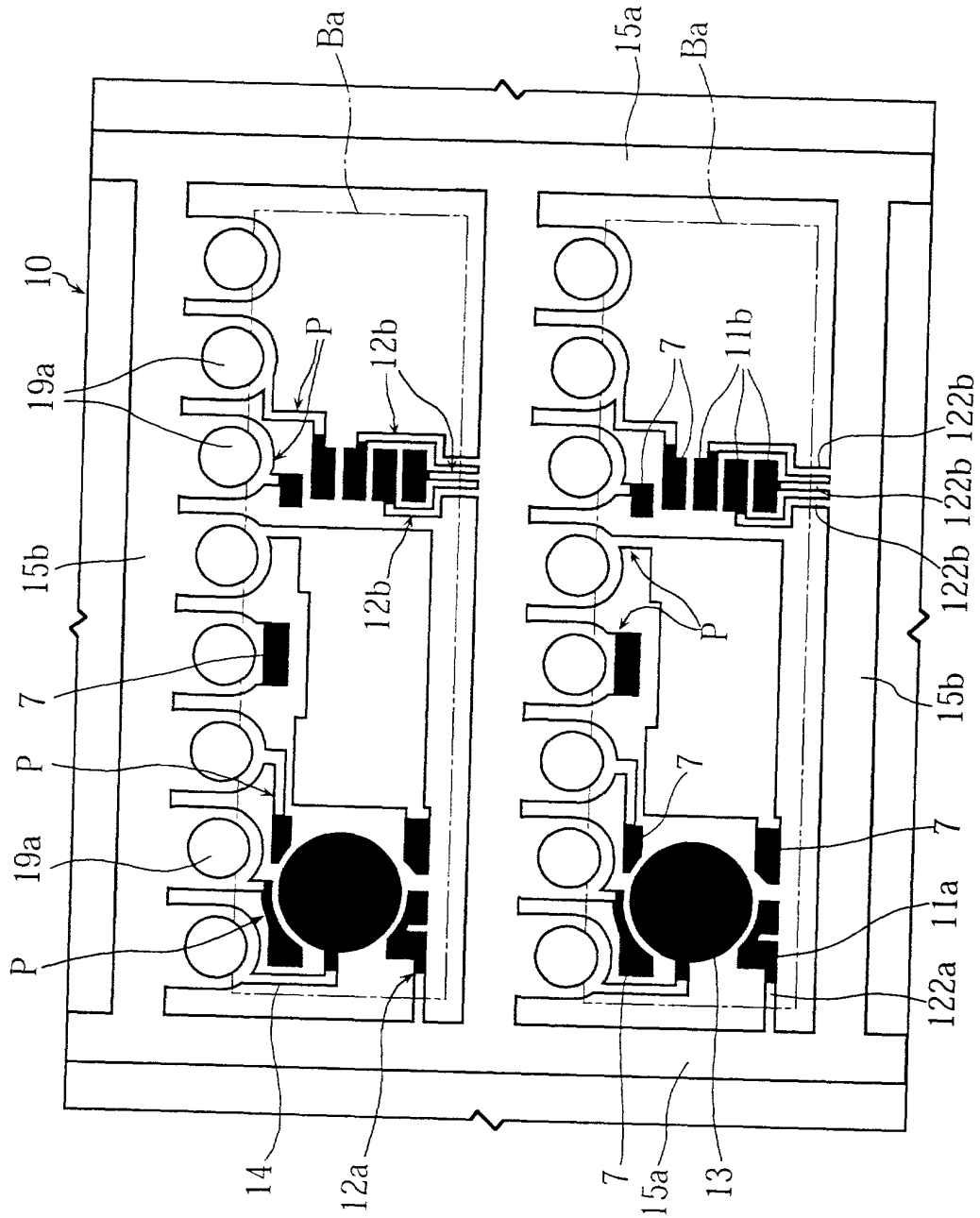


FIG. 11

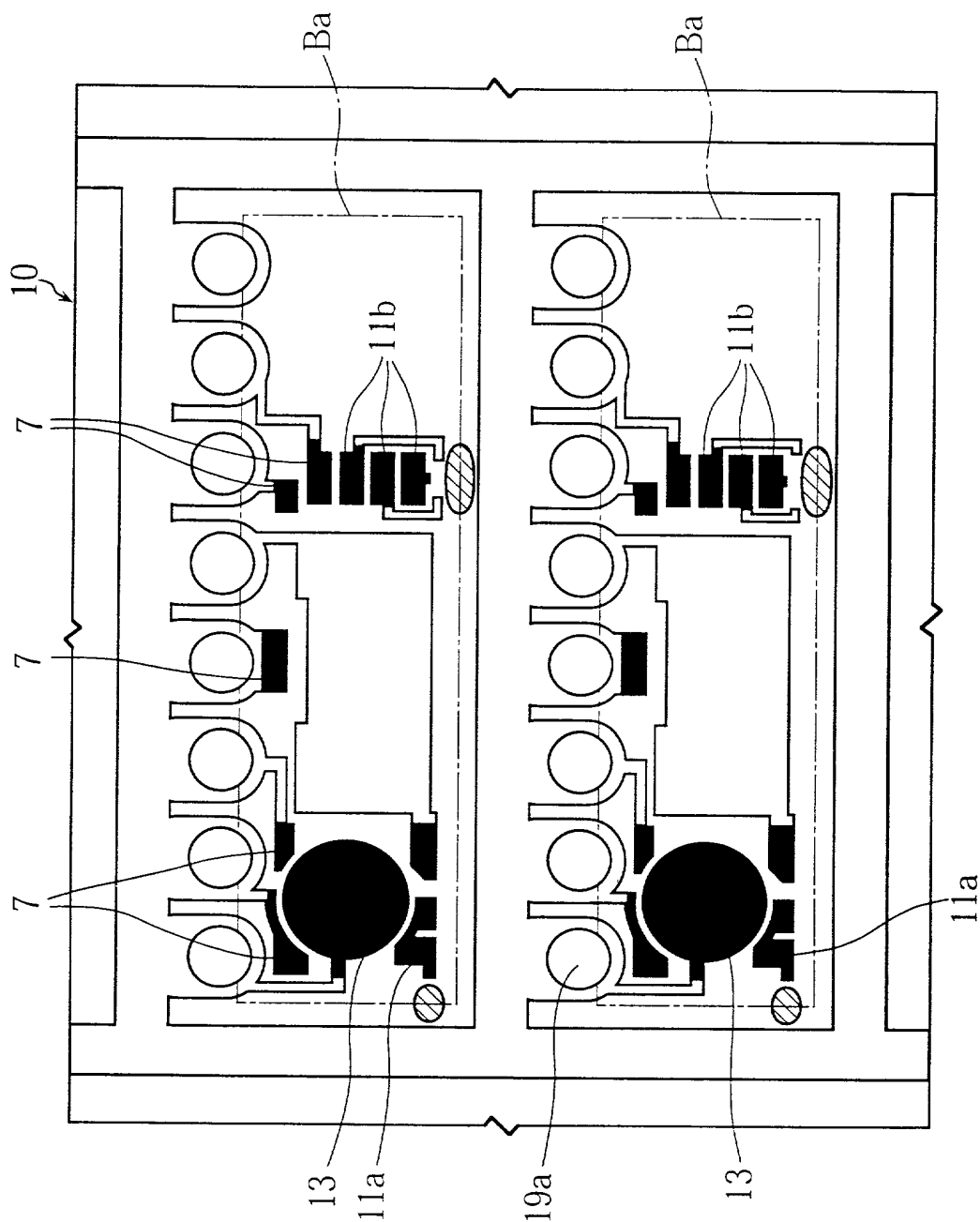


FIG. 12

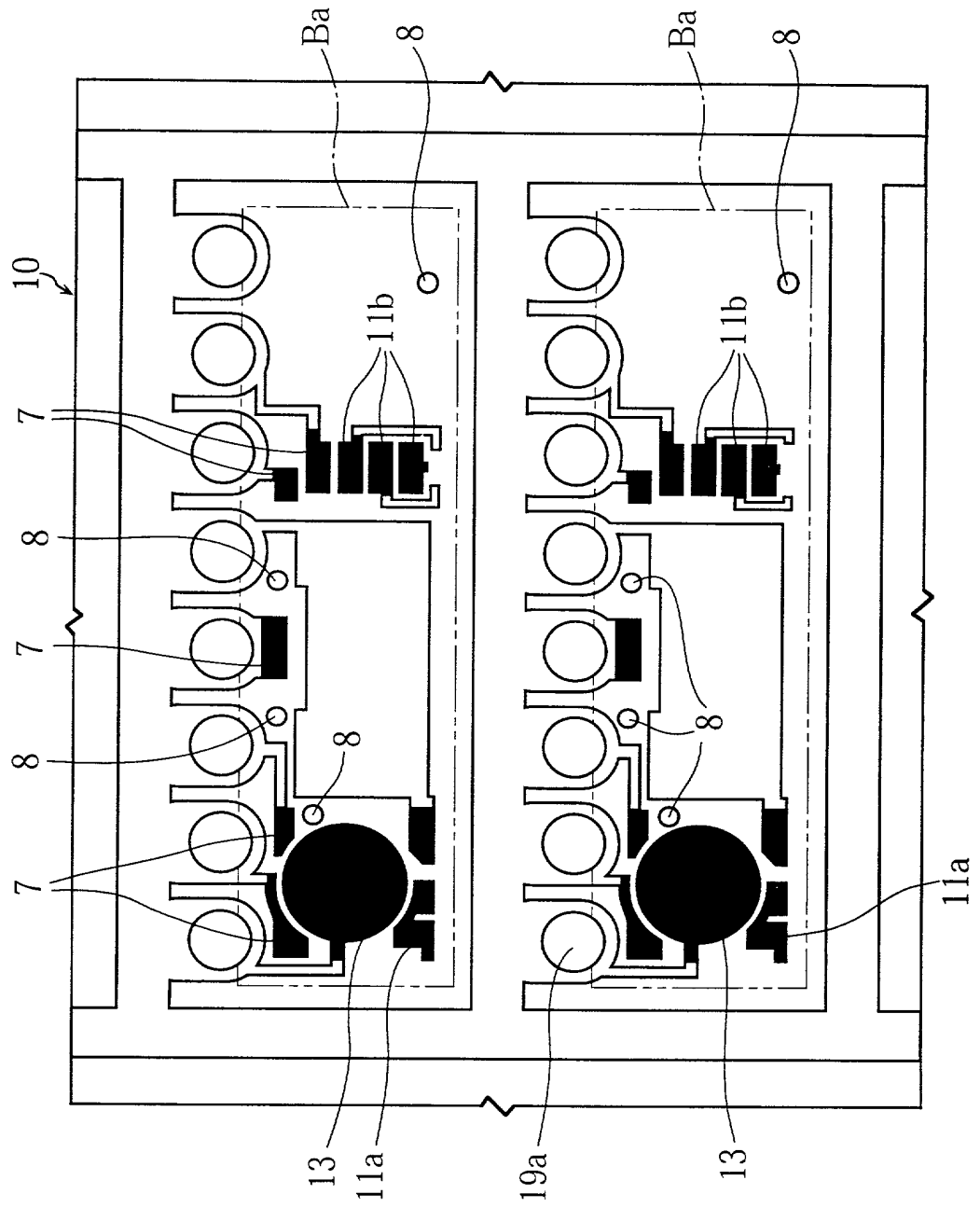


FIG. 13

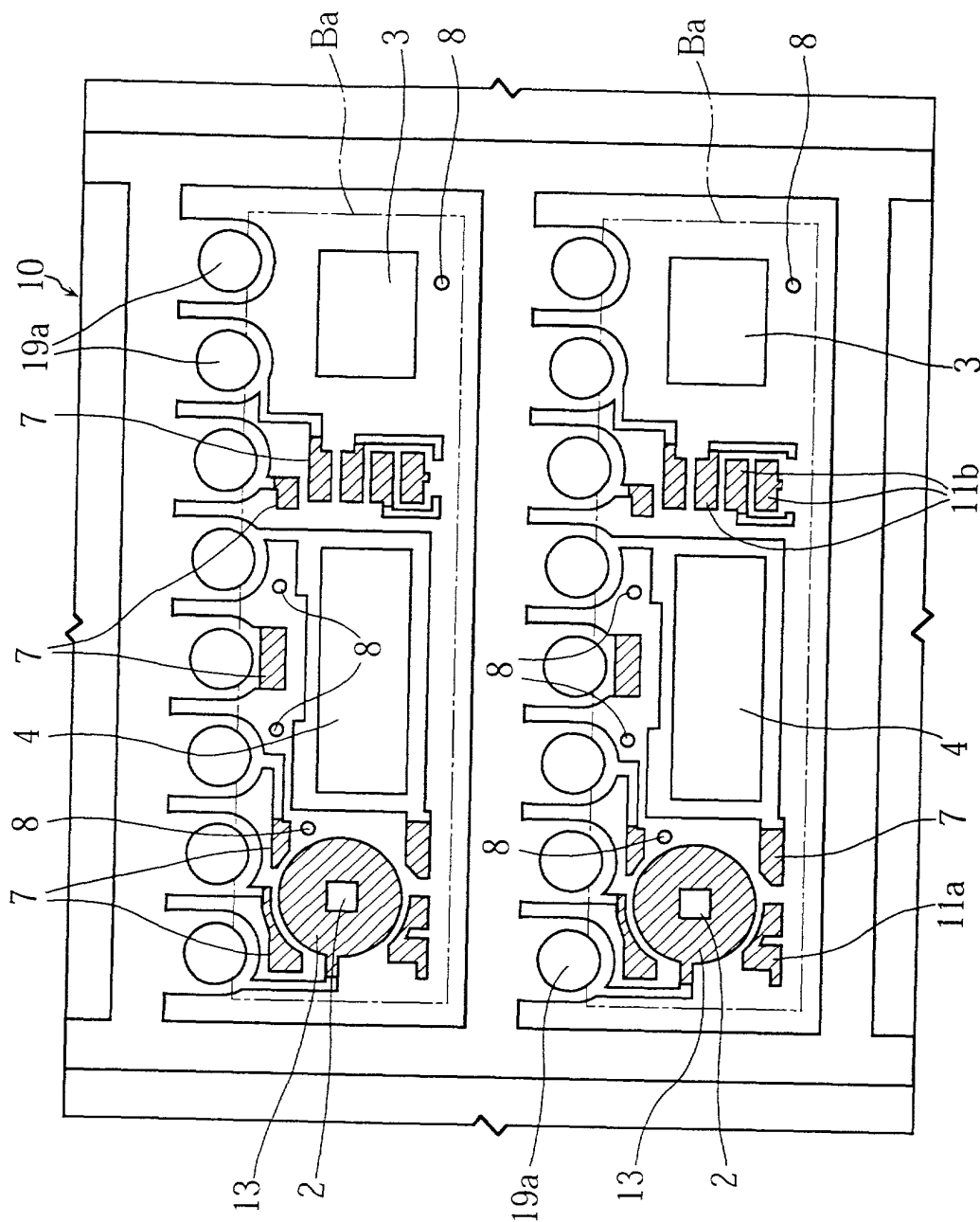


FIG. 14

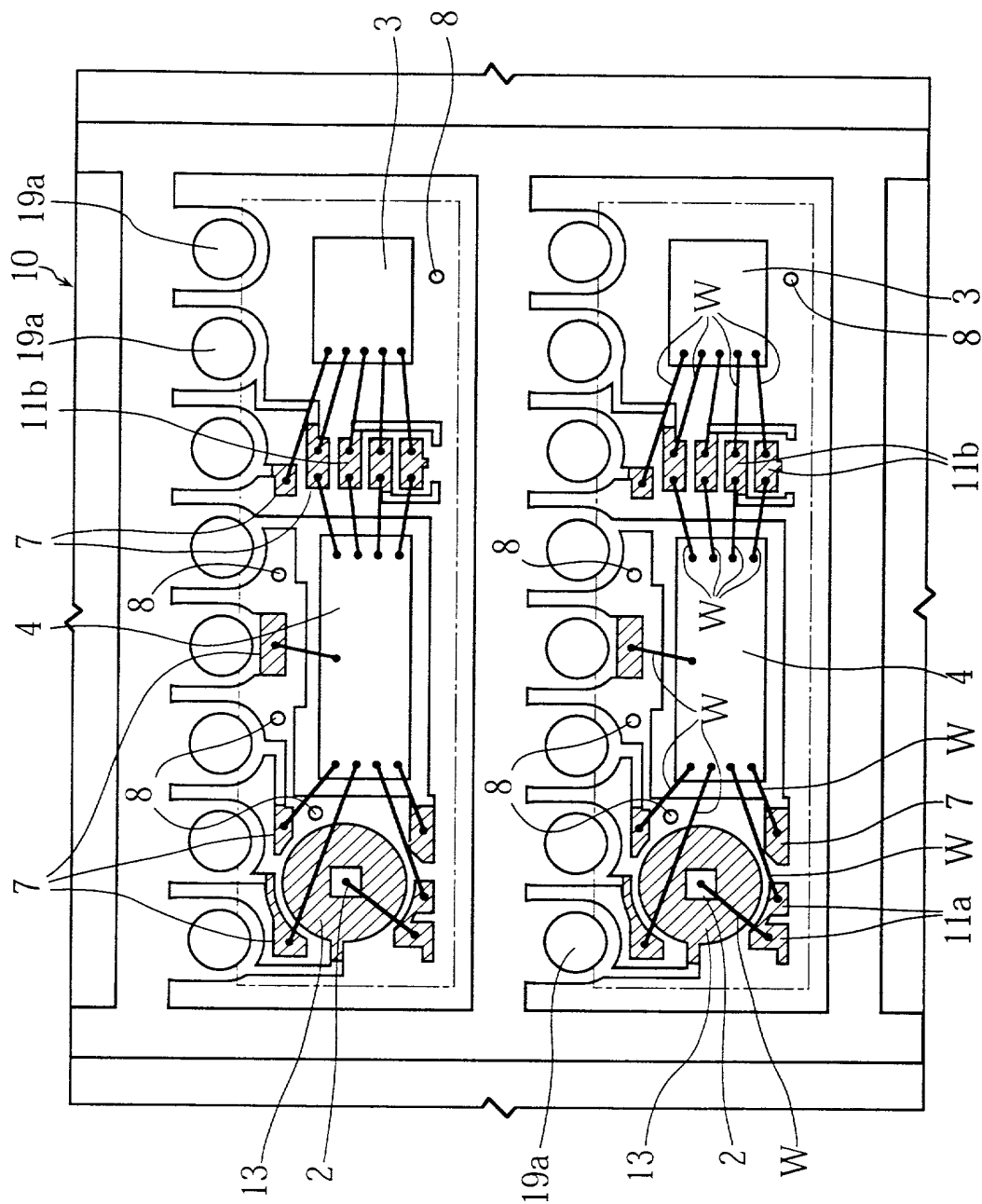


FIG. 15

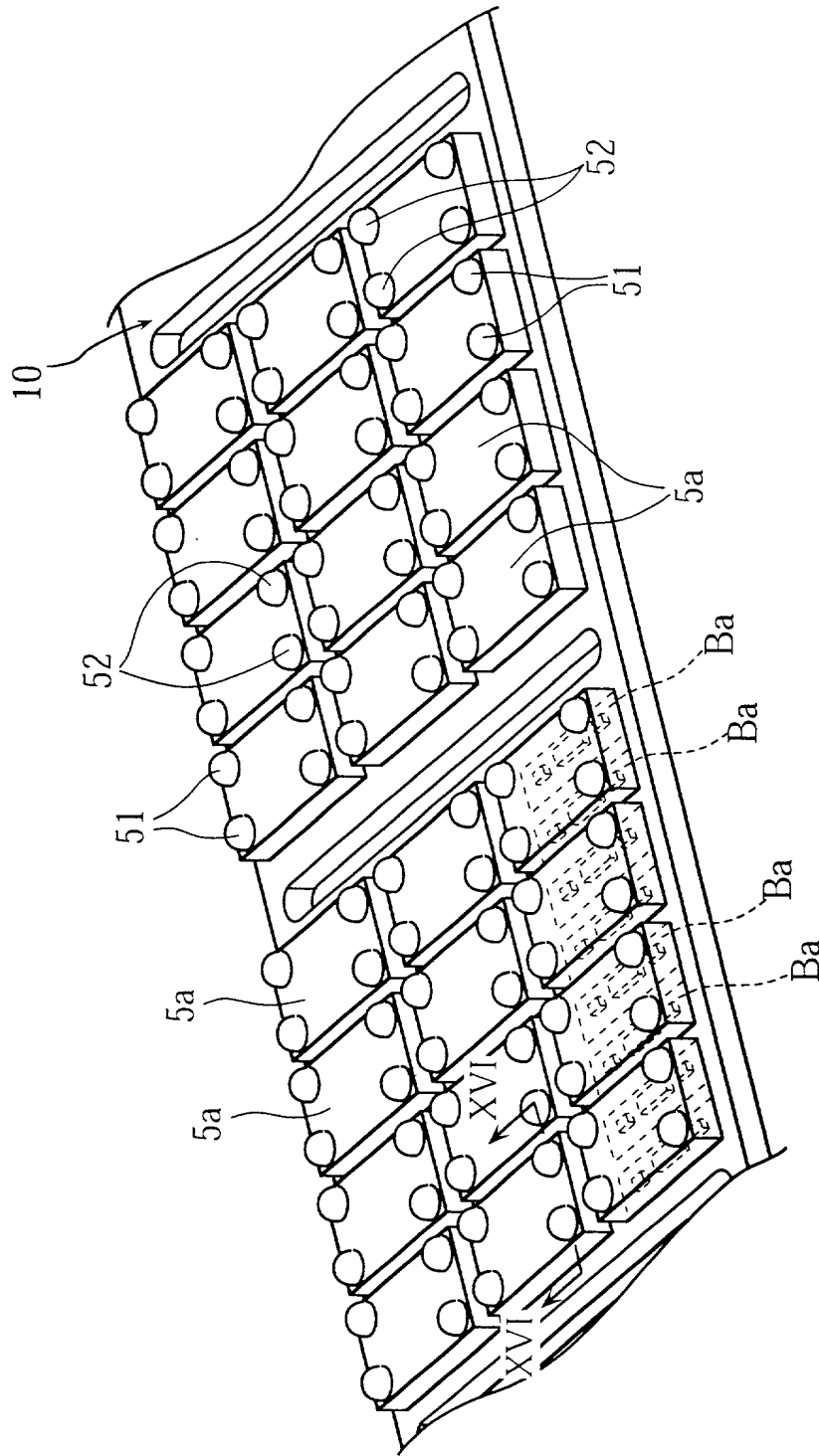
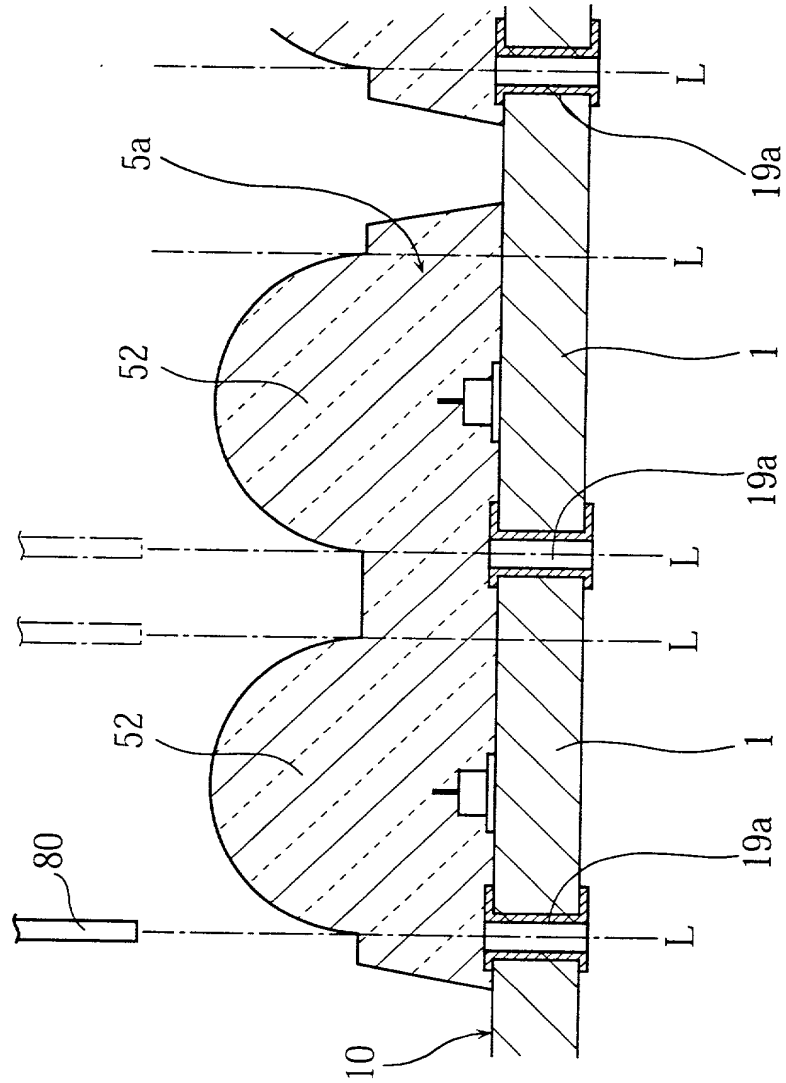


FIG. 16







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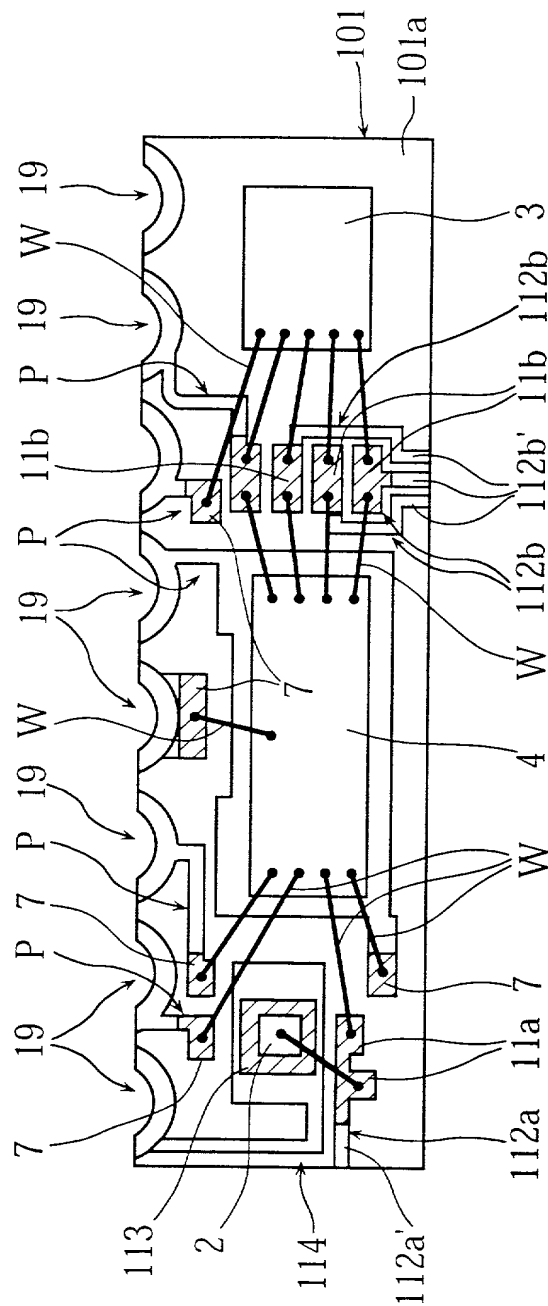
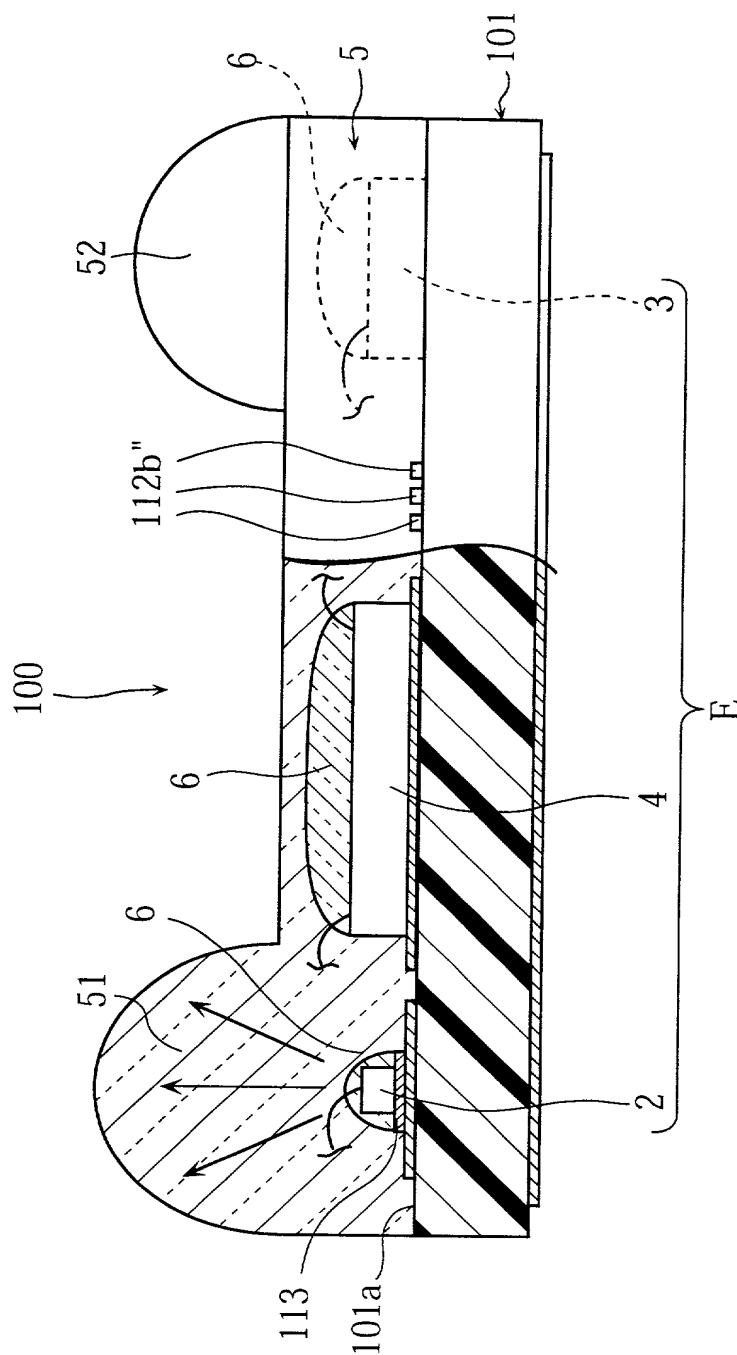


FIG. 19



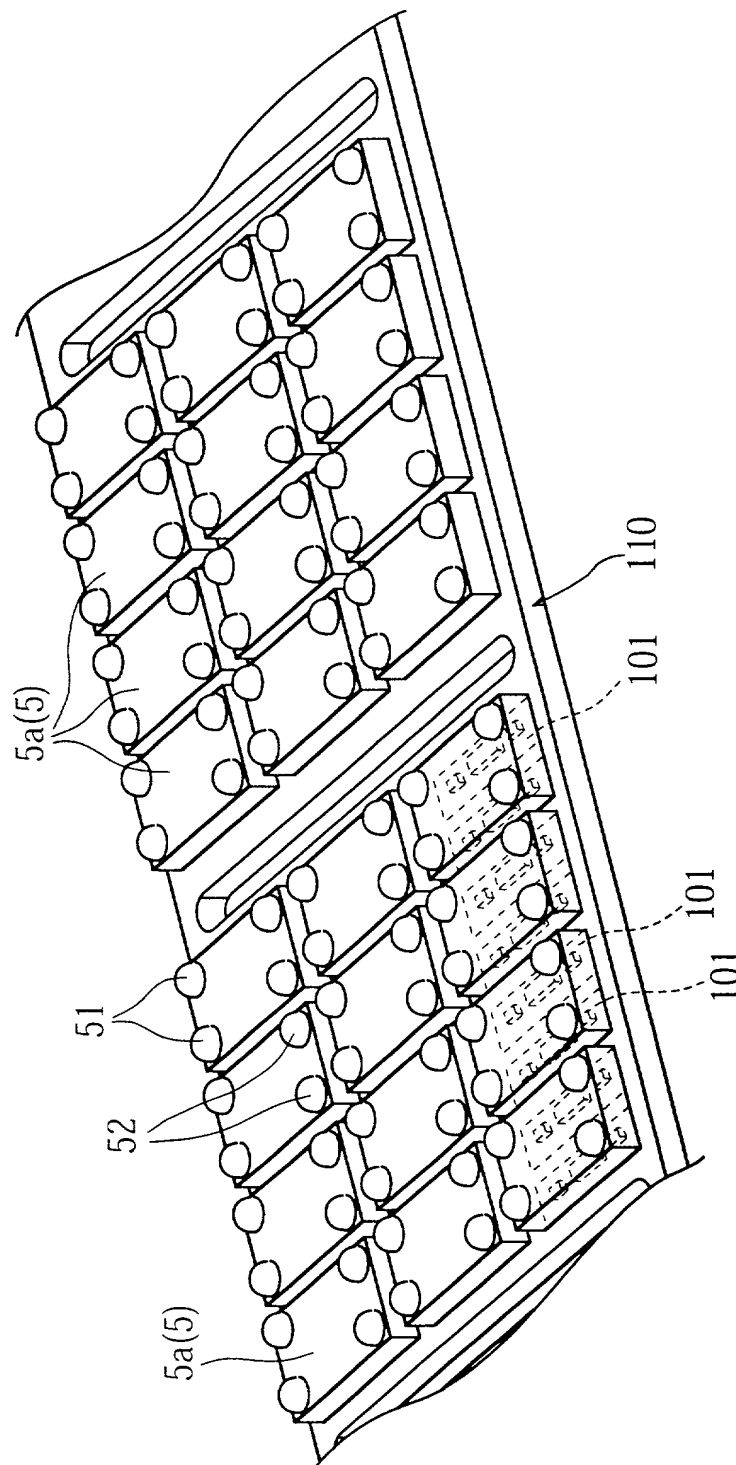


FIG. 20